

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application for:

Kazunari Honma et al.

Application No.: 10/631,858

Patent No.: 7,247,900

For: DIELECTRIC DEVICE HAVING
DIELECTRIC FILM TERMINATED
BY HALOGEN ATOMS

Examiner: Howard Weiss

Art Unit: 2814

Filing Date: August 1, 2003

Confirmation No.: 9152

Customer No.: 60172

Mail Stop Certificate of Corrections Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 CFR 1.323

Dear Commissioner:

Upon review of the above-referenced Letters Patent, an error was noted that was the mistake of the U.S. Patent and Trademark Office.

Please correct the following:

At the Title Page, item 56, under "References Cited" section,

--OTHER PUBLICATIONS

Item I "Low Temperature Deposition Material", Section 4 "New Deposition Material", Ferroelectric Memory Advanced Process, September 13, 1999-- should be added.

This non-patent literature (NPL) document was considered in the form PTO-1449 initialed by the Examiner on April 23, 2007, but this NPL document was incorrectly omitted in the front page of the issued patent.

Since the error is by the U.S. Patent Office, it is believed that no fee is required for these corrections. It is respectfully requested that a Certificate of Correction be issued.

The Commissioner is hereby authorized to charge shortages or credit overpayments to Deposit Account No. 500393.

Respectfully submitted,
SCHWABE, WILLIAMSON & WYATT, P.C.

Dated: January 19, 2010

/Dennis M. de Guzman/
Dennis M. de Guzman
Reg. No. 41,702

U.S. Bank Centre
1420 5th Avenue, Suite 3010
Seattle, Washington 98101
Telephone: 206-622-1711

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

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PATENT NO. : 7,247,900

APPLICATION NO.: 10/631,858

ISSUE DATE : 07-24-2007

INVENTOR(S) : Honma et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page, item 56, under "References Cited" section,
--Item I "Low Temperature Deposition Material"
Section 4 "New Deposition Material"
Ferroelectric Memory Advanced Process
September 13, 1999-- should be added

MAILING ADDRESS OF SENDER (Please do not use customer number below):

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Seattle, WA 98101

This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. **SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

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